

RBN75H65T1FPQ-A0

650V - 75A - IGBT
Power Switching

R07DS1383EJ0120
Rev.1.20
Aug.03.2020

Features

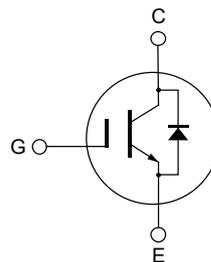
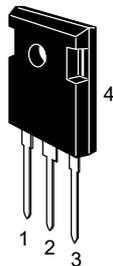
- Trench gate and thin wafer technology (G8H series)
- Built in fast recovery diode in one package
- Low collector to emitter saturation voltage
 $V_{CE(sat)} = 1.5 \text{ V typ. (at } I_C = 75 \text{ A, } V_{GE} = 15 \text{ V, } T_a = 25^\circ\text{C)}$
- Quality grade: Standard
- High speed switching
- Non-specification for short circuit
- Applications: UPS, Welding, photovoltaic inverters, Power converter system

Key Performance

| Type | V_{CES} | I_C | $V_{CE(sat)}, T_C=25^\circ\text{C}$ | I_F | T_J |
|------------------|-----------|-------|-------------------------------------|-------|--------|
| RBN75H65T1FPQ-A0 | 650 V | 75 A | 1.5 V | 50 A | 175 °C |

Outline

RENESAS Package code: PRSS0003ZH-A
(Package name: TO-247A)



1. Gate
2. Collector
3. Emitter
4. Collector

Absolute Maximum Ratings

(T_c = 25°C)

| Item | Symbol | Ratings | Unit |
|------------------------------|--|----------------|------|
| Collector to emitter voltage | V _{CES} | 650 | V |
| Gate to emitter voltage | V _{GES} | ±30 | V |
| Collector current | T _c = 25 °C | I _C | A |
| | T _c = 100 °C | I _C | A |
| Collector peak current | I _{C(peak)} ^{Notes1} | 300 | A |
| Diode forward current | T _c = 25 °C | I _F | A |
| | T _c = 100 °C | I _F | A |
| Diode forward peak current | I _{F(peak)} ^{Notes1} | 300 | A |
| Collector power dissipation | P _C ^{Notes2} | 312 | W |
| Junction temperature | T _J ^{Notes2} | 175 | °C |
| Storage temperature | T _{stg} | -55 to +150 | °C |

Note: Continuous heavy condition (e.g. high temperature/voltage/current or high variation of temperature) may affect a reliability even if it is within the absolute maximum ratings. Please consider derating condition for appropriate reliability in reference Renesas Semiconductor Reliability Handbook (Recommendation for Handling and Usage of Semiconductor Devices) and individual reliability data.

Notes: 1. PW ≤ 10 μs, duty cycle ≤ 1%

2. Please use this device in the thermal conditions which the junction temperature does not exceed 175 °C.
Renesas IGBT Application Note is disclosed about reliability test and application condition up to 175 °C.

Thermal Resistance Characteristics

(T_c = 25°C)

| Item | Symbol | Max. Value ^{Notes3} | Unit |
|---|----------------------|------------------------------|------|
| Junction to case thermal resistance (IGBT) | R _{th(j-c)} | 0.48 | °C/W |
| Junction to case thermal resistance (Diode) | R _{th(j-c)} | 0.73 | °C/W |

Notes: 3. Designed target value on Renesas measurement condition. (Not tested)

Electrical Characteristics

(T_c = 25°C)

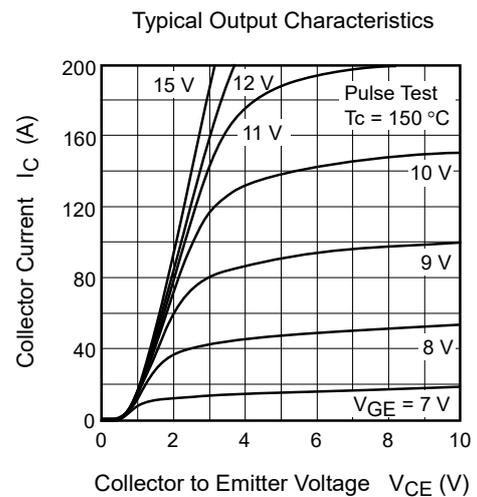
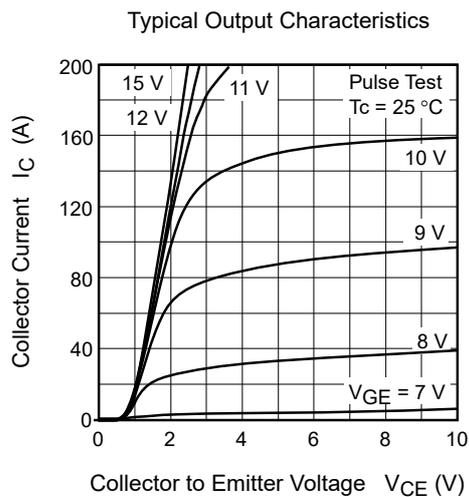
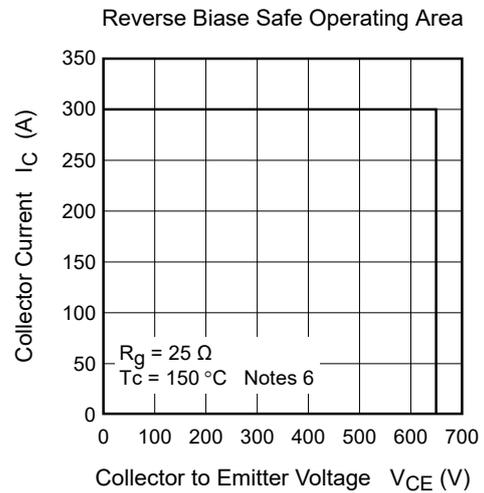
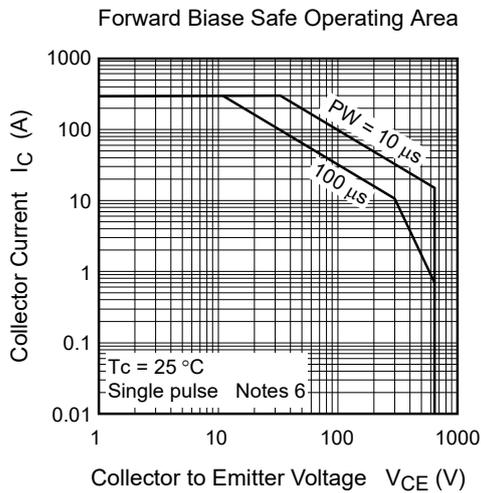
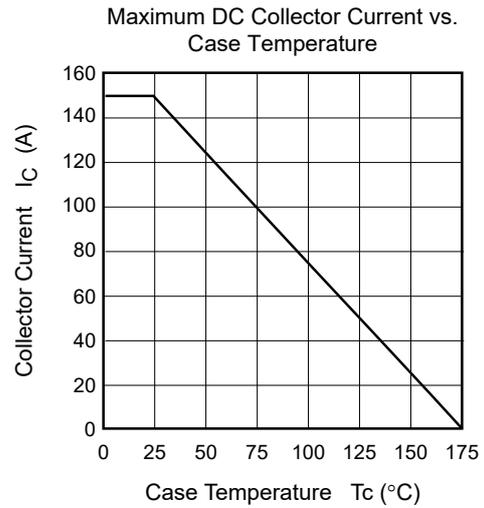
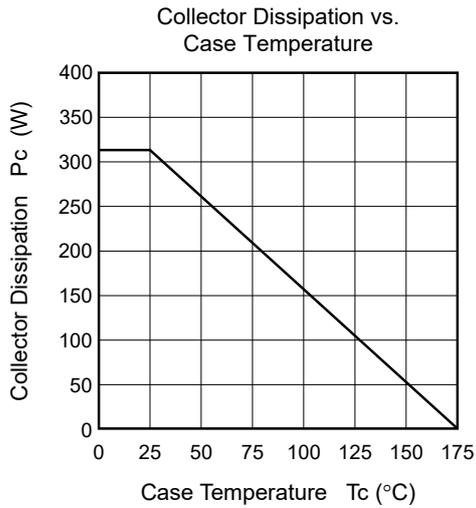
| Item | Symbol | Min | Typ | Max | Unit | Test Conditions |
|---|----------------------|-----|------|-----|------|---|
| Collector to emitter leakage current | I _{CES} | — | — | 200 | μA | V _{CE} = 650 V, V _{GE} = 0 V |
| Gate to emitter leakage current | I _{GES} | — | — | ±1 | μA | V _{GE} = ±30 V, V _{CE} = 0 V |
| Gate to emitter threshold voltage | V _{GE(th)} | 4.1 | — | 5.9 | V | V _{CE} = 10 V, I _C = 1.5 mA |
| Collector to emitter saturation voltage | V _{CE(sat)} | — | 1.5 | 2.0 | V | I _C = 75 A, V _{GE} = 15 V ^{Notes4} |
| Input capacitance | C _{ies} | — | 1500 | — | pF | V _{CE} = 25 V |
| Output capacitance | C _{oes} | — | 190 | — | pF | V _{GE} = 0 V |
| Reverse transfer capacitance | C _{res} | — | 16 | — | pF | f = 1 MHz |
| Total gate charge | Q _g | — | 54 | — | nC | V _{GE} = 15 V |
| Gate to emitter charge | Q _{ge} | — | 13 | — | nC | V _{CE} = 400 V |
| Gate to collector charge | Q _{gc} | — | 24 | — | nC | I _C = 75 A |
| Turn-on delay time | t _{d(on)} | — | 29 | — | ns | V _{CC} = 400 V |
| Rise time | t _r | — | 27 | — | ns | V _{GE} = +15 V/-5 V |
| Turn-off delay time | t _{d(off)} | — | 113 | — | ns | I _C = 75 A |
| Fall time | t _f | — | 37 | — | ns | R _g = 16 Ω |
| Turn-on loss energy | E _{on} | — | 1.6 | — | mJ | T _C = 25 °C |
| Turn-off loss energy | E _{off} | — | 1.0 | — | mJ | Inductive load ^{Notes5} |
| Total switching energy | E _{total} | — | 2.6 | — | mJ | |
| Turn-on delay time | t _{d(on)} | — | 27 | — | ns | V _{CC} = 400 V |
| Rise time | t _r | — | 24 | — | ns | V _{GE} = +15 V/-5V |
| Turn-off delay time | t _{d(off)} | — | 137 | — | ns | I _C = 75 A |
| Fall time | t _f | — | 55 | — | ns | R _g = 16 Ω |
| Turn-on loss energy | E _{on} | — | 2.3 | — | mJ | T _C = 150 °C |
| Turn-off loss energy | E _{off} | — | 1.5 | — | mJ | Inductive load ^{Notes5} |
| Total switching energy | E _{total} | — | 3.8 | — | mJ | |

| | | | | | | |
|-------------------------------------|-----------------|---|-----|-----|----|---|
| Diode forward voltage | V _F | — | 1.7 | 2.2 | V | I _F = 50 A ^{Notes4} |
| Diode reverse recovery time | t _{rr} | — | 72 | — | ns | I _F = 50 A, di _F /dt = 300 A/μs |
| Diode reverse recovery charge | Q _{rr} | — | 0.3 | — | μC | |
| Diode peak reverse recovery current | I _{rr} | — | 8 | — | A | |

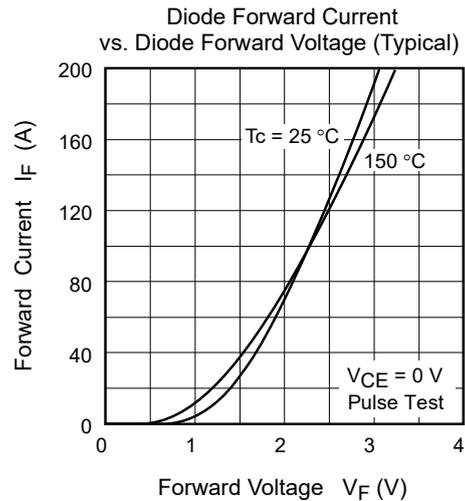
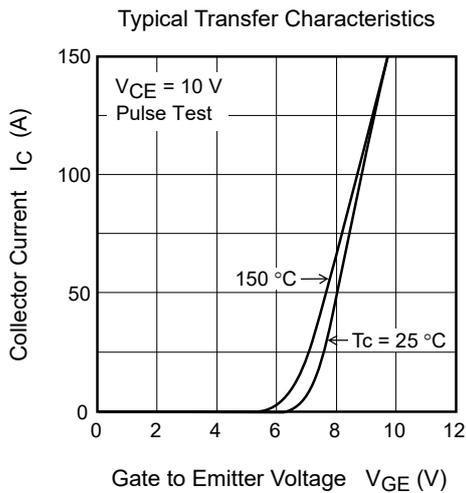
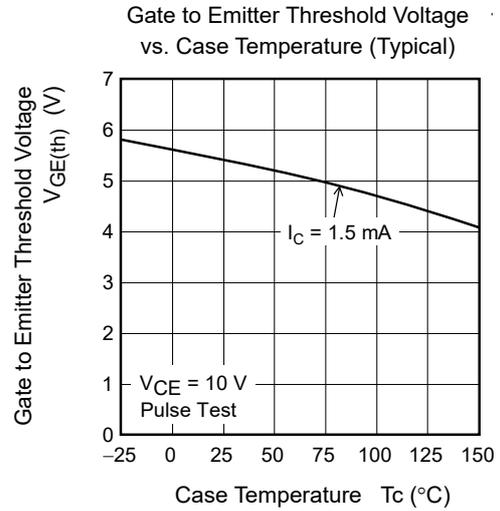
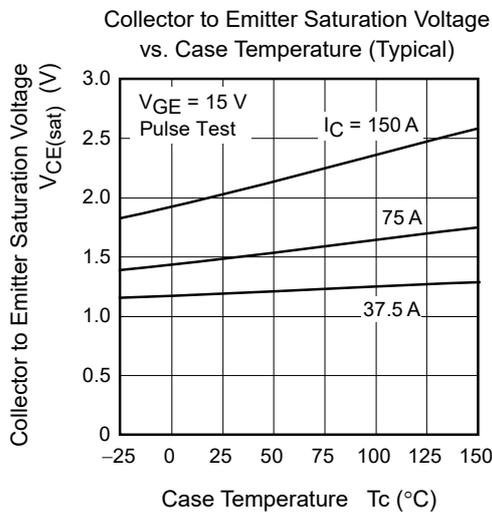
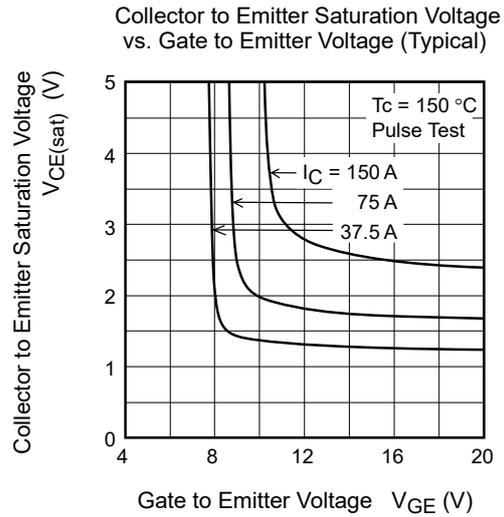
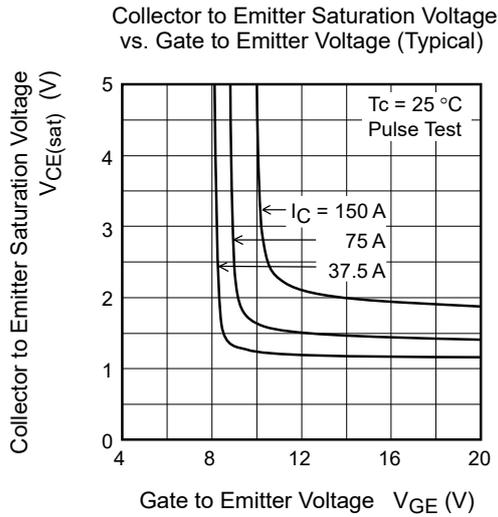
Notes: 4. Pulse test

5. Switching time test circuit and waveform are shown below.

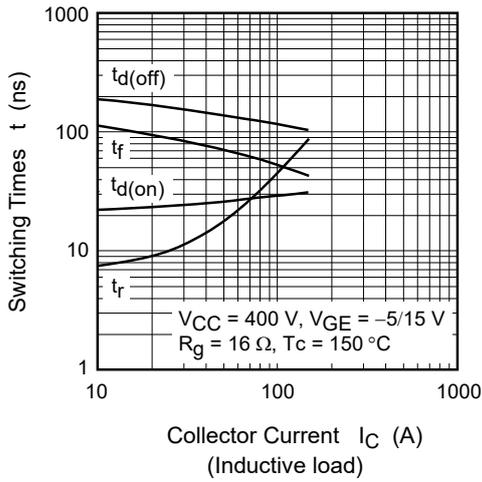
Main Characteristics



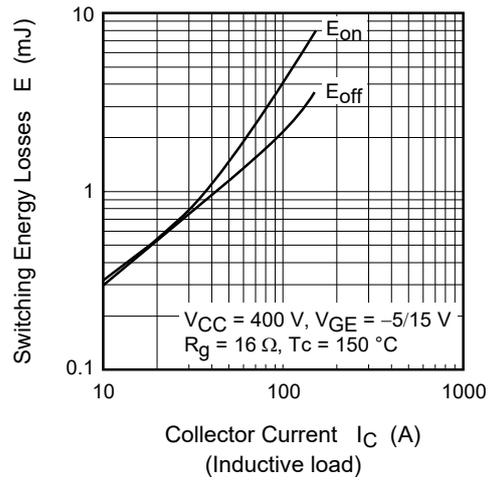
Notes: 6. Designed target value on Renesas measurement condition. (Not tested)
 Renesas recommends that operating conditions are designed according to a document "Power MOS FET · IGBT Attention of Handling Semiconductor Devices".



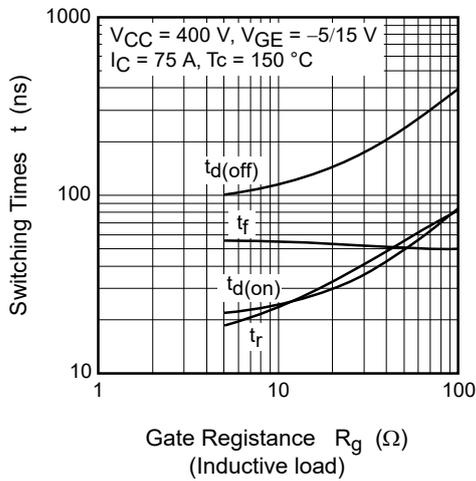
Switching Characteristics (Typical) (1)



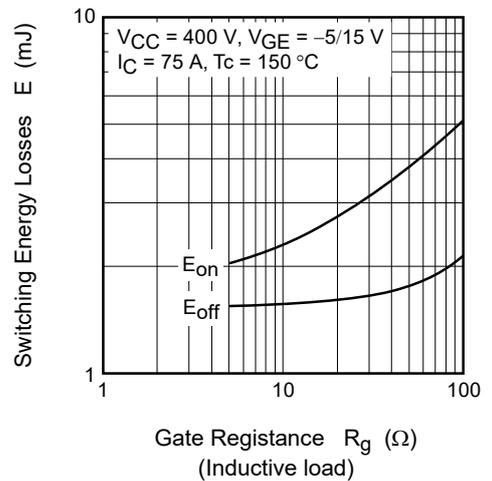
Switching Characteristics (Typical) (2)



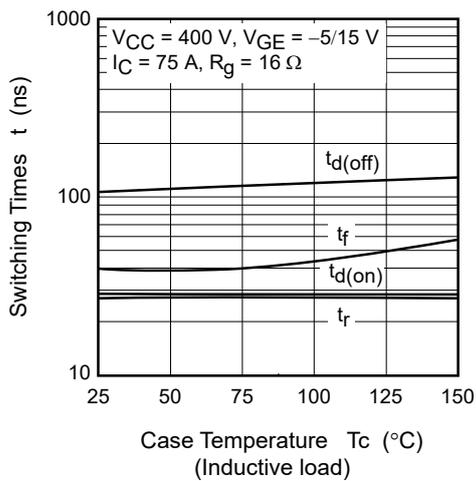
Switching Characteristics (Typical) (3)



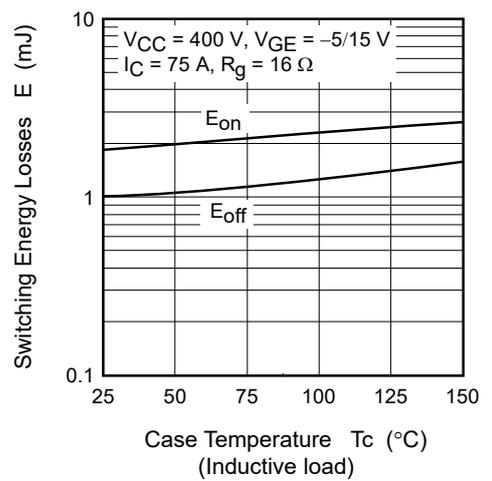
Switching Characteristics (Typical) (4)

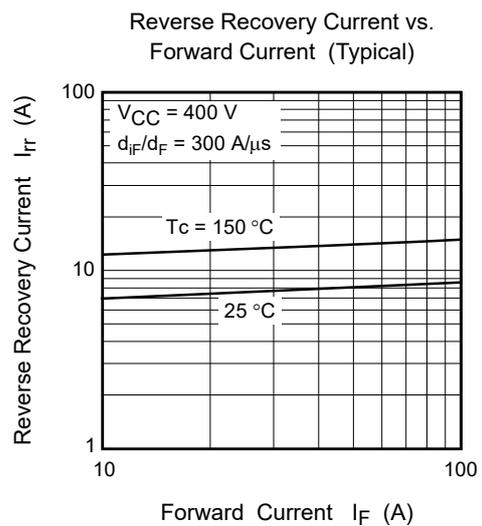
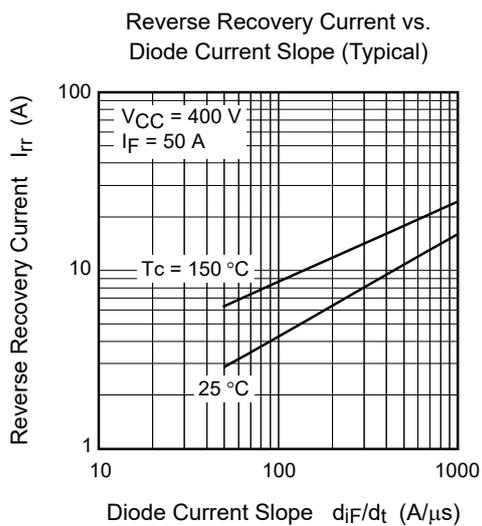
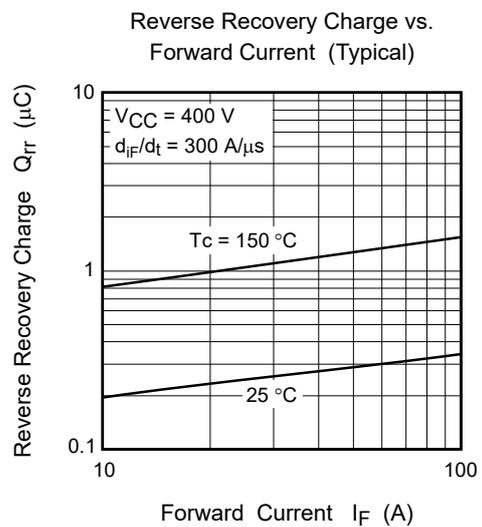
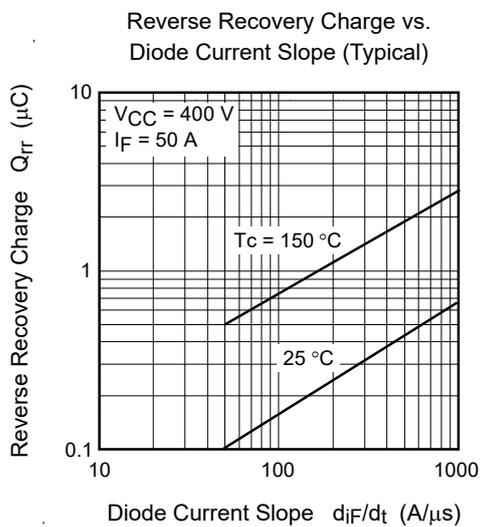
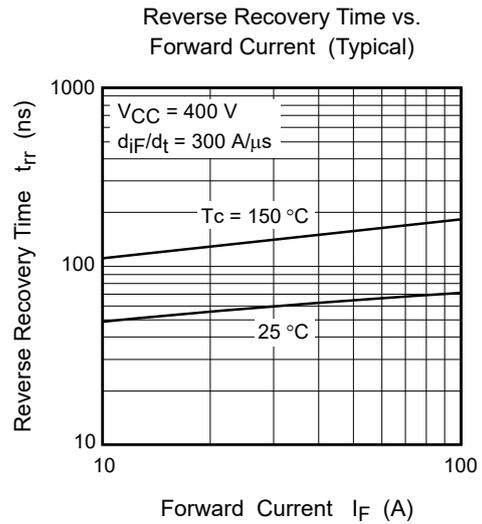
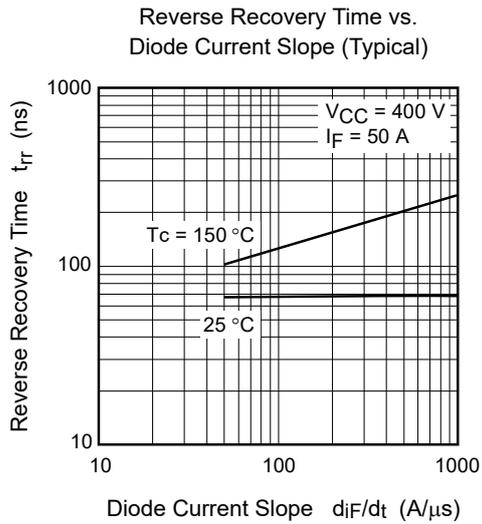


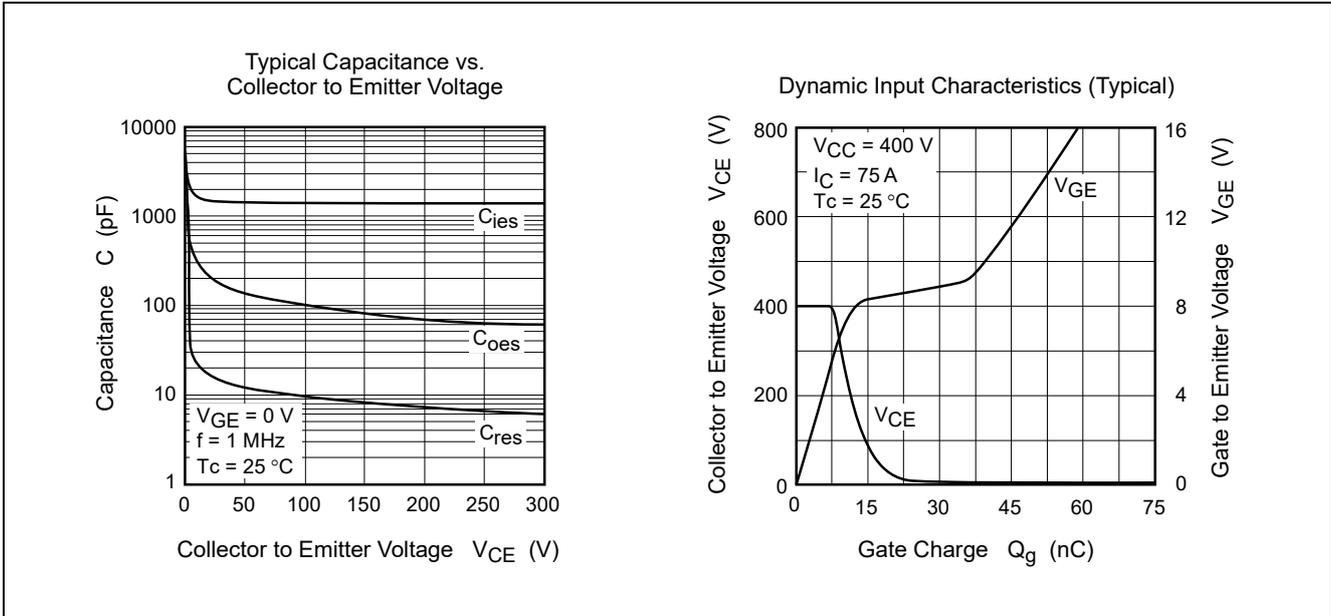
Switching Characteristics (Typical) (5)

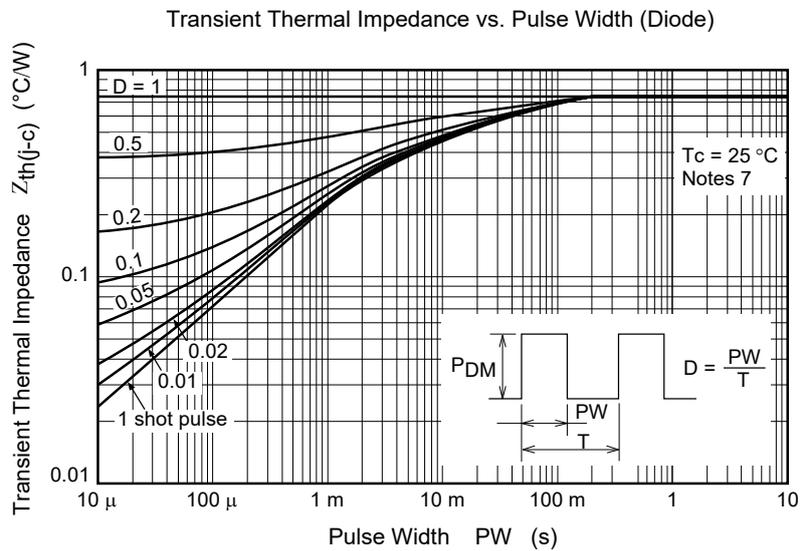
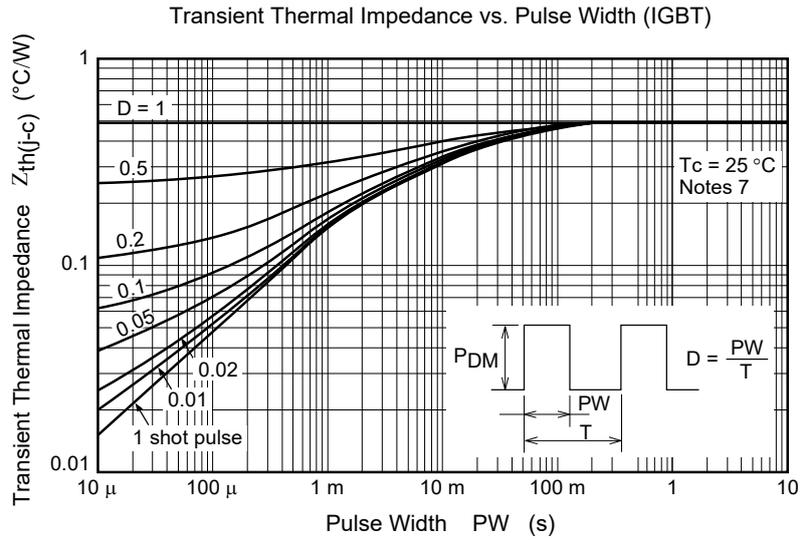


Switching Characteristics (Typical) (6)



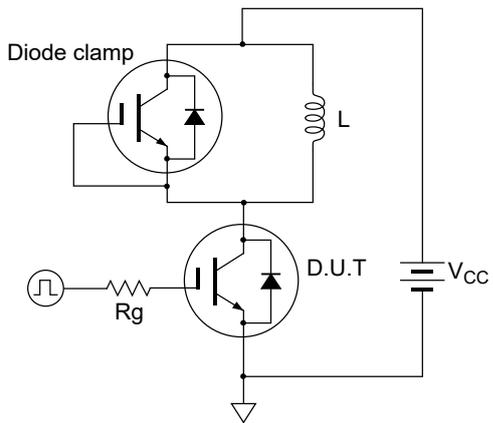




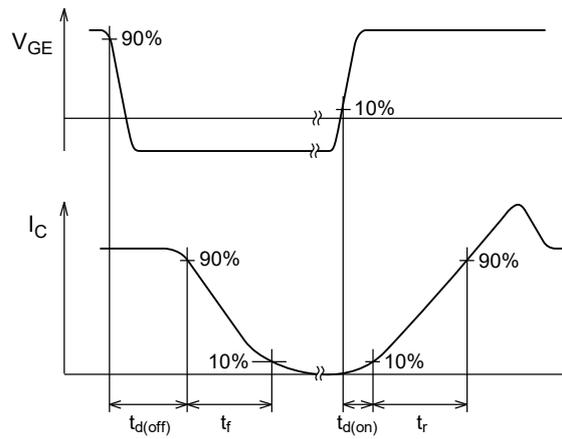


Notes: 7. Designed target value on Renesas measurement condition. (Not tested)

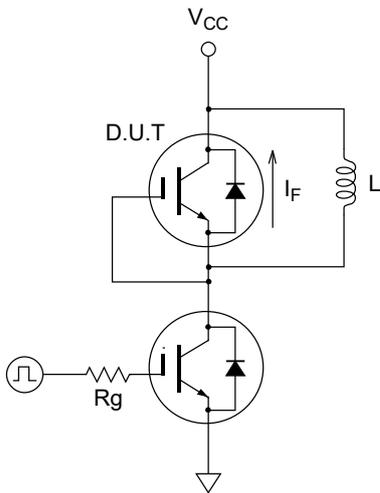
Switching Time Test Circuit



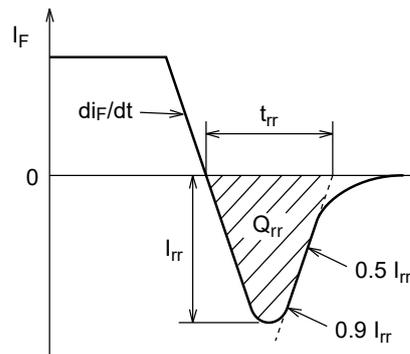
Waveform



Diode Reverse Recovery Time Test Circuit



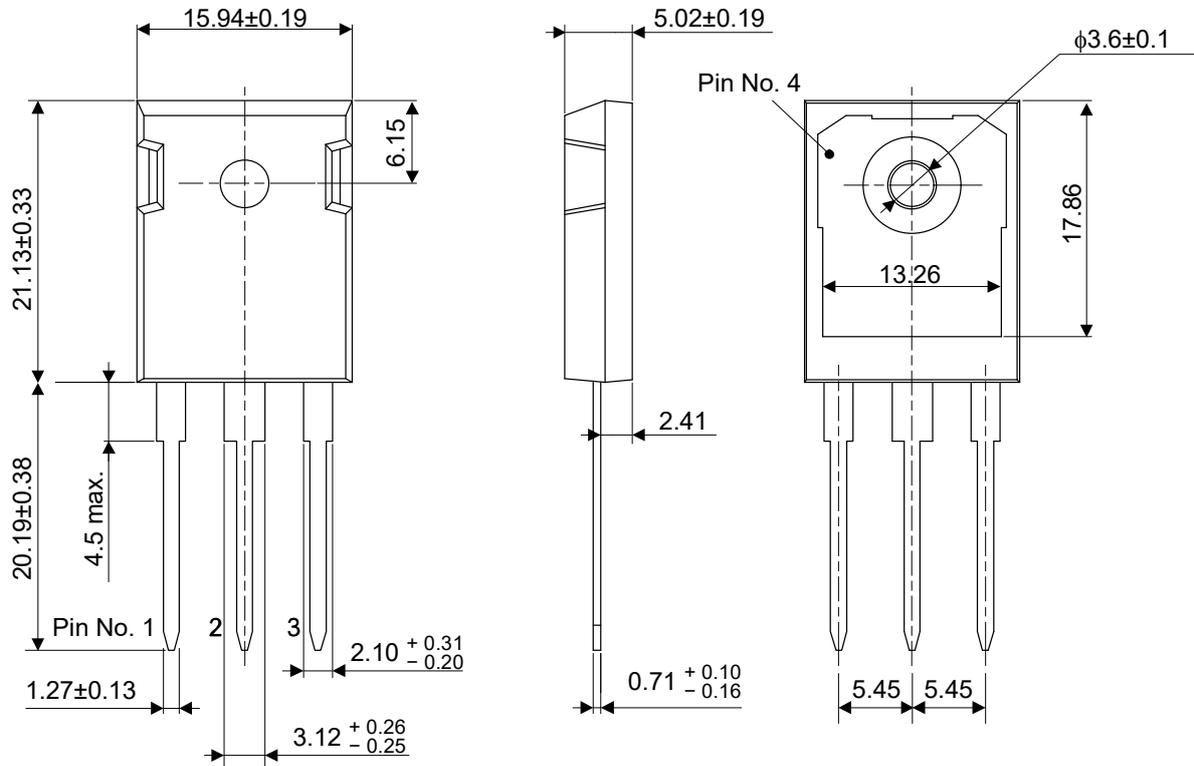
Waveform



Package Dimensions

| JEDEC Package Code | RENESAS Code | Previous Code | MASS (Typ) [g] |
|--------------------|--------------|---------------|----------------|
| TO-247AD | PRSS0003ZH-A | — | 6.14 |

Unit: mm



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Ordering Information

| Orderable Part Number | Quantity | Shipping Container |
|-----------------------|----------|--------------------|
| RBN75H65T1FPQ-A0#CB0 | 240 pcs | Box (Tube) |

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